

Notice of References Cited	Application/Control No. 10/505,219		Applicant(s)/Patent Under Reexamination HOSONO ET AL.	
	Examiner Matthew W. Such		Art Unit 2891	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	B	US-2002/0096687	07-2002	Kuo et al.	257/99
*	C	US-5,530,267	06-1996	Brandle et al.	257/76
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	L	US-			
	M	US-			

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Takano, Y., et al. "Single Crystal Growth of (LaO)CuS." J. OF ALLOYS & CMPDS. Vol. 249 (1997): pp. 221-223.
	V	Ishikawa, K., et al. "Preparation and Electrical Properties of (LaO)AgS and (LnO)CuS (Ln = La, Pr, or Nd)." J. ELECTROCHEM. SOC. Vol. 138 (1991): pp. 1166-1170.
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	X	Ueda, K., et al. "Room-Temperature Excitons in Wide-Gap Layered-Oxysulfide Semiconductor: LaCuOS." APPL. PHYS. LETT. Vol. 78 (2001): pp. 2333-2335.

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.